

# RJK0852DPB

80V, 30A,  $12m\Omega$  max. Silicon N Channel Power MOS FET Power Switching

R07DS0080EJ0200 Rev.2.00 Apr 09, 2013

#### **Features**

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting

Low on-resistance

 $R_{DS(on)} = 9 \text{ m}\Omega \text{ typ. (at } V_{GS} = 10 \text{ V})$ 

- Pb-free
- Halogen-free

#### **Outline**

RENESAS Package code: PTZZ0005DA-A (Package name: LFPAK)

5
D
4
Godff
1, 2, 3 Source
4 Gate
5 Drain

## **Applications**

• Switching Mode Power Supply

### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	80	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	30	А
Drain peak current	I <sub>D(pulse)</sub> Note1	120	А
Body-drain diode reverse drain current	I <sub>DR</sub>	30	А
Avalanche current	I <sub>AP</sub> Note 2	15	А
Avalanche energy	E <sub>AS</sub> Note 2	30	mJ
Channel dissipation	Pch Note3	55	W
Channel to Case Thermal Resistance	θch-C	2.27	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$ 

3. Tc = 25°C

This product is for the low voltage drive ( $\leq 10V$ ).

If the driving voltage is over 10 V under normal conditions, please use the product for high gate to source cutoff voltage  $(V_{GS(off)})$  which characteristics has been improved.

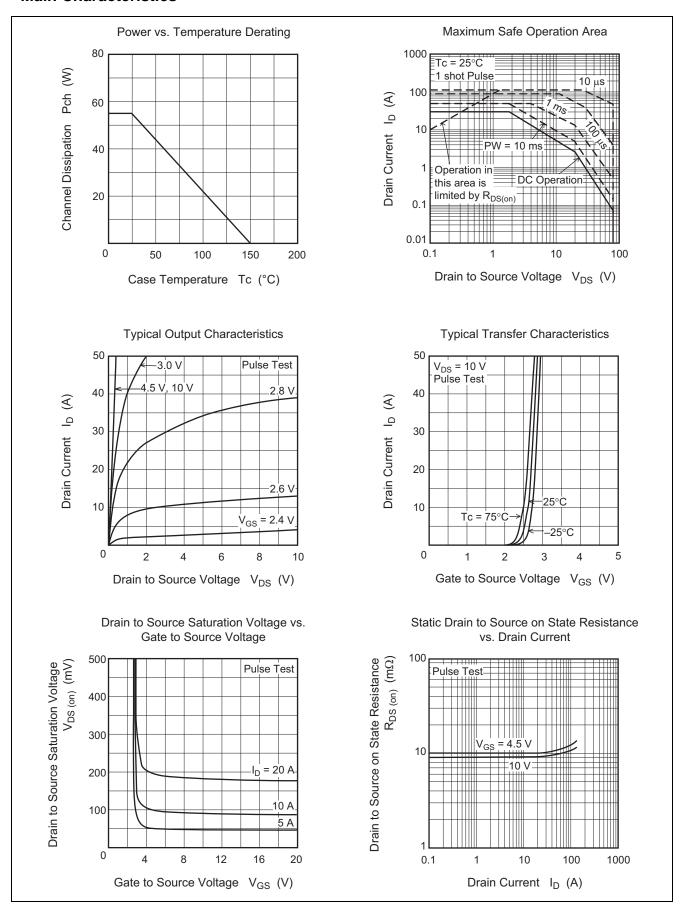
## **Electrical Characteristics**

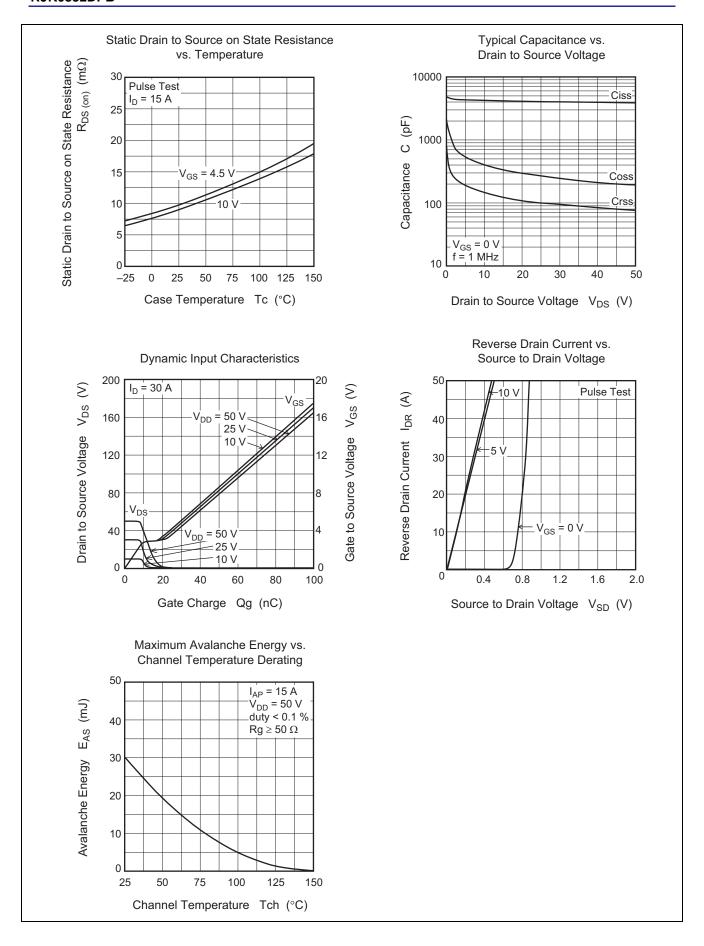
 $(Ta = 25^{\circ}C)$ 

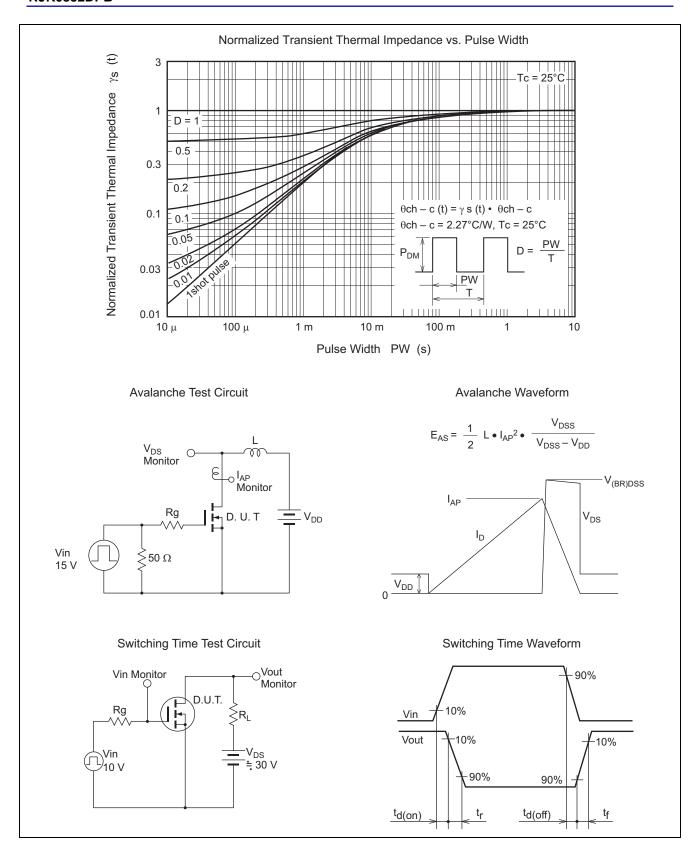
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	80	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$
Gate to source leak current	$I_{GSS}$	_	_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$
Gate to source cutoff voltage	$V_{GS(off)}$	1.2	_	2.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state	R <sub>DS(on)</sub>	_	9	12	mΩ	$I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
resistance	R <sub>DS(on)</sub>	_	10	14	mΩ	$I_D = 15 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y <sub>fs</sub>	_	50	_	S	$I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	4150	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$
Output capacitance	Coss	_	417	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss		164	_	pF	
Gate Resistance	Rg		0.4	_	Ω	
Total gate charge	Qg	_	28	_	nC	$V_{DD} = 25 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_{D} = 30 \text{ A}$
Gate to source charge	Qgs	_	13	_	nC	
Gate to drain charge	Qgd	_	7.6	_	nC	
Turn-on delay time	t <sub>d(on)</sub>	_	11	_	ns	$\begin{aligned} V_{GS} &= 10 \text{ V}, \text{ I}_D = 15 \text{ A}, \\ V_{DD} &\cong 30 \text{ V}, \text{ R}_L = 2 \Omega, \\ Rg &= 4.7 \Omega \end{aligned}$
Rise time	t <sub>r</sub>	_	5.4	_	ns	
Turn-off delay time	t <sub>d(off)</sub>	_	56	_	ns	
Fall time	t <sub>f</sub>	_	8.2	_	ns	
Body-drain diode forward voltage	$V_{DF}$	_	0.83	1.1	V	$I_F = 30 \text{ A}, V_{GS} = 0 \text{ V}^{Note4}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	38	_	ns	$I_F = 30 \text{ A}, V_{GS} = 0 \text{ V}$ $di_F/dt = 100 \text{ A}/ \mu \text{s}$

Notes: 4. Pulse test

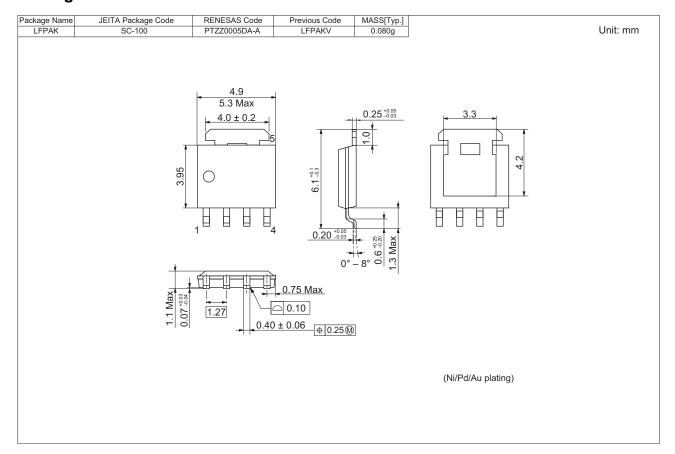
#### **Main Characteristics**







## **Package Dimensions**



## **Ordering Information**

Part No.	Quantity	Shipping Container
RJK0852DPB-00-J5	2500 pcs	Taping

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